

AMENDMENTS TO THE CLAIMS

1. (currently amended) A method for forming LED, comprising the steps of:
forming an LED epitaxial layer on a provisional substrate;
etching said LED epitaxial layer to form LED chips ~~by means of photolithography~~;
forming a reflecting layer on said LED chips;
forming a metal layer on said reflecting layer;
removing said provisional substrate to expose surfaces of said LED chips;
forming pads on said surfaces of said LED chips; and
separating said metal layer to form individual LED chips by means of mechanical force.
2. (original) The method in claim 1, wherein a material of said reflecting layer is Ag, Al, Rh, Pt, Pd, Ni, Ti, Co, Au, or the combination thereof.
3. (original) The method in claim 1, wherein said metal layer is formed by means of electroplating, electroless plating, chemical vapor deposition, or the combination thereof.
4. (original) The method in claim 1, wherein said metal layer is formed by means of a physical vapor deposition.
5. (original) The method in claim 4, wherein said physical vapor deposition is evaporation, sputtering deposition, or the combination thereof.
6. (original) The method in claim 1, wherein said provisional substrate is removed by means of polishing, etching, laser ablation, or the combination thereof.
7. (original) The method in claim 1, wherein a material of said metal layer is Cu, Al, Ni, Mo, W, Ag, Au, Ti, Co, Pd, Pt, Fe, or the combination thereof.

8. (original) The method in claim 1, wherein a thickness of said metal layer is more than 30 μ m.
9. (original) The method in claim 1, wherein a thickness of said metal layer between said every two LED chips is 5-30 μ m.
10. (currently amended) A method for forming LED, comprising the steps of:
forming an LED epitaxial layer on a provisional substrate;
forming a reflecting layer on said LED epitaxial layer;
forming a metal layer on said reflecting layer;
etching said LED epitaxial layer, said reflecting layer, and said metal layer to form LED chips ~~by means of photolithography~~;
removing said provisional substrate to expose surfaces of said LED chips; and
forming pads on said surfaces of said LED chips.
11. (original) The method in claim 10, wherein a material of said reflecting layer is Ag, Al, Rh, Pt, Pd, Ni, Ti, Co, Au, or the combination thereof.
12. (original) The method in claim 10, wherein said metal layer is formed by means of electroplating, electroless plating, chemical vapor deposition, or the combination thereof.
13. (original) The method in claim 10, wherein said metal layer is formed by means of a physical vapor deposition.
14. (original) The method in claim 13, wherein said physical vapor deposition is evaporation, sputtering deposition, or the combination thereof.
15. (original) The method in claim 10, wherein said provisional substrate is removed by means of polishing, etching, laser ablation, or the combination thereof.

16. (original) The method in claim 10, wherein a material of said metal layer is Cu, Al, Ni, Mo, W, Ag, Au, Ti, Co, Pd, Pt, Fe, or the combination thereof.
17. (original) The method in claim 10, wherein a thickness of said metal layer is more than 30 μ m.